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Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	83
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l162vct6a

List of tables

Table 1.	Device summary	1
Table 2.	Ultra-low-power STM32L162xC/C-A device features and peripheral counts	10
Table 3.	Functionalities depending on the operating power supply range	14
Table 4.	CPU frequency range depending on dynamic voltage scaling	15
Table 5.	Functionalities depending on the working mode (from Run/active down to standby)	16
Table 6.	Timer feature comparison	27
Table 7.	Legend/abbreviations used in the pinout table	35
Table 8.	STM32L162xC/C-A pin definitions	35
Table 9.	Alternate function input/output	44
Table 10.	Voltage characteristics	56
Table 11.	Current characteristics	56
Table 12.	Thermal characteristics	57
Table 13.	General operating conditions	57
Table 14.	Embedded reset and power control block characteristics	58
Table 15.	Embedded internal reference voltage calibration values	60
Table 16.	Embedded internal reference voltage	60
Table 17.	Current consumption in Run mode, code with data processing running from Flash	62
Table 18.	Current consumption in Run mode, code with data processing running from RAM	63
Table 19.	Current consumption in Sleep mode	64
Table 20.	Current consumption in Low-power run mode	65
Table 21.	Current consumption in Low-power sleep mode	66
Table 22.	Typical and maximum current consumptions in Stop mode	67
Table 23.	Typical and maximum current consumptions in Standby mode	69
Table 24.	Peripheral current consumption	70
Table 25.	Low-power mode wakeup timings	73
Table 26.	High-speed external user clock characteristics	73
Table 27.	Low-speed external user clock characteristics	75
Table 28.	HSE oscillator characteristics	76
Table 29.	LSE oscillator characteristics ($f_{LSE} = 32.768$ kHz)	77
Table 30.	HSI oscillator characteristics	79
Table 31.	LSI oscillator characteristics	79
Table 32.	MSI oscillator characteristics	80
Table 33.	PLL characteristics	82
Table 34.	RAM and hardware registers	82
Table 35.	Flash memory and data EEPROM characteristics	83
Table 36.	Flash memory and data EEPROM endurance and retention	83
Table 37.	EMS characteristics	84
Table 38.	EMI characteristics	85
Table 39.	ESD absolute maximum ratings	85
Table 40.	Electrical sensitivities	86
Table 41.	I/O current injection susceptibility	86
Table 42.	I/O static characteristics	87
Table 43.	Output voltage characteristics	88
Table 44.	I/O AC characteristics	89
Table 45.	NRST pin characteristics	90
Table 46.	TIMx characteristics	91
Table 47.	I ² C characteristics	92

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L162xC/C-A ultra-low-power ARM® Cortex®-M3 based microcontroller product line.

The STM32L162xC/C-A microcontrollers feature 256 Kbytes of Flash memory.

The ultra-low-power STM32L162xC/C-A devices are available in 4 different package types: from 64 pins to 144 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L162xC/C-A microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, wired and wireless sensors, video intercom
- Utility metering

This STM32L162xC/C-A datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The application note “Getting started with STM32L1xxxx hardware development” (AN3216) gives a hardware implementation overview. Both documents are available from the STMicroelectronics website www.st.com.

For information on the ARM® Cortex®-M3 core please refer to the ARM® Cortex®-M3 technical reference manual, available from the www.arm.com website. [Figure 1](#) shows the general block diagram of the device family.

2.1 Device overview

Table 2. Ultra-low-power STM32L162xC/C-A device features and peripheral counts

Peripheral		STM32L162RC-A	STM32L162VC-A	STM32L162QC	STM32L162ZC
Flash (Kbytes)		256			
Data EEPROM (Kbytes)		8			
RAM (Kbytes)		32			
AES		1			
Timers	32 bit	1			
	General-purpose	6			
	Basic	2			
Communication interfaces	SPI	8(3) ⁽¹⁾			
	I ² S	2			
	I ² C	2			
	USART	3			
	USB	1			
GPIOs		51	83	109	115
Operation amplifiers		2			
12-bit synchronized ADC Number of channels		1 21	1 25	1 40	1 40
12-bit DAC Number of channels		2 2			
LCD (STM32L152xx devices only) COM x SEG		1 4x32 or 8x28	1 4x44 or 8x40		
Comparators		2			
Capacitive sensing channels		23			
Max. CPU frequency		32 MHz			
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option			
Operating temperatures		Ambient operating temperature: -40 °C to 85 °C / -40 °C to 105 °C Junction temperature: -40 to + 110 °C			
Packages		LQFP64	LQFP100	UFBGA132	LQFP144

1. 5 SPIs are USART configured in synchronous mode emulating SPI master.

3.1 Low-power modes

The ultra-low-power STM32L162xC/C-A devices support dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71 V - 3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4 MHz (generated only with the multispeed internal RC oscillator clock source)

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.
- **Low-power run mode**
This mode is achieved with the multispeed internal (MSI) RC oscillator set to the minimum clock (131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In low-power run mode, the clock frequency and the number of enabled peripherals are both limited.
- **Low-power sleep mode**
This mode is achieved by entering Sleep mode with the internal voltage regulator in Low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.
When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.
- **Stop mode with RTC**
Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.
The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.

power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using USART1, USART2 or USB. See Application note "STM32 microcontroller system memory boot mode" (AN2606) for details.

Table 8. STM32L162xC/C-A pin definitions (continued)

Pins					Pin name	Pin Type ⁽¹⁾	I / O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP144	UFBGA132	LQFP100	LQFP64	WL CSP64					Alternate functions	Additional functions
27	J2	16	9	F8	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
28	-	17	10	D6	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
-	J3	-	-	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
-	K1	-	-	-		I	-		-	-
29	K2	18	11	F7	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP/
30	J1	19	12	E7	V _{SSA}	S	-	V _{SSA}	-	-
31	-	20	-	-	V _{REF-}	S	-	V _{REF-}	-	-
32	L1	21	-	-	V _{REF+}	S	-	V _{REF+}	-	-
33	M1	22	13	G8	V _{DDA}	S	-	V _{DDA}	-	-
34	L2	23	14	F6	PA0-WKUP1	I/O	FT	PA0	TIM2_CH1_ETR/ TIM5_CH1/ USART2_CTS	WKUP1/ RTC_TAMP2/ ADC_IN0/ COMP1_INP
35	M2	24	15	E6	PA1	I/O	FT	PA1	TIM2_CH2/TIM5_CH2/ USART2_RTS/ LCD_SEG0	ADC_IN1/ COMP1_INP/ OPAMP1_VINP
36	-	25	16	H8	PA2	I/O	FT	PA2	TIM2_CH3/TIM5_CH3/ TIM9_CH1/ USART2_TX/LCD_SEG1	ADC_IN2/ COMP1_INP/ OPAMP1_VINM
-	K3	-	-	-	PA2	I/O	FT	PA2	TIM2_CH3/TIM5_CH3/ TIM9_CH1/ USART2_TX/LCD_SEG1	ADC_IN2/ COMP1_INP
-	M3	-	-	-	OPAMP1_VI NM	I	TC	OPAMP1_ VINM	-	-
37	L3	26	17	G7	PA3	I/O	TC	PA3	TIM2_CH4/TIM5_CH4/ TIM9_CH2/ USART2_RX/LCD_SEG2	ADC_IN3/ COMP1_INP/ OPAMP1_VOUT
38	-	27	18	F5	V _{SS_4}	S	-	V _{SS_4}	-	-



Table 9. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	..	AFIO11	AFIO12	..	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3	-		LCD	-		CPRI	SYSTEM
PF6	-	-	TIM5_ETR	-	-	-	-	-	-		-	-		-	EVENT OUT
PF7	-	-	TIM5_CH2	-	-	-	-	-	-		-	-		-	EVENT OUT
PF8	-	-	TIM5_CH3	-	-	-	-	-	-		-	-		-	EVENT OUT
PF9	-	-	TIM5_CH4	-	-	-	-	-	-		-	-		-	EVENT OUT
PF10	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PF11	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PF12	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PF13	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PF14	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PF15	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG0	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG1	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG2	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG3	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG4	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT

5

Figure 7. Memory map



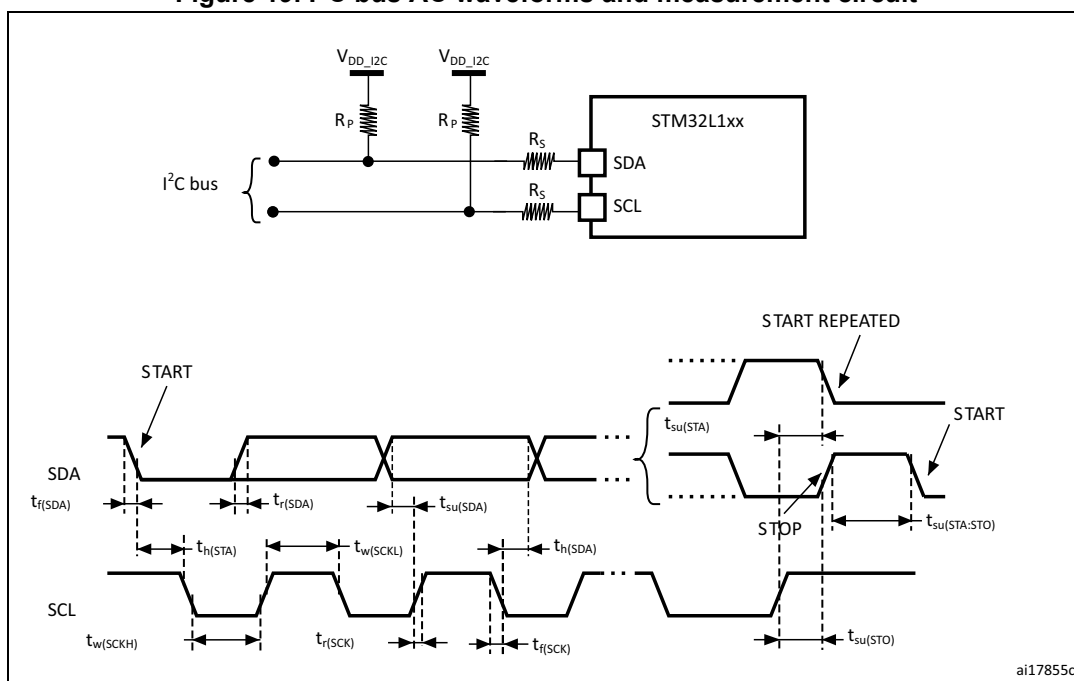
Table 24. Peripheral current consumption⁽¹⁾ (continued)

Peripheral		Typical consumption, V _{DD} = 3.0 V, T _A = 25 °C				Unit
		Range 1, V _{CORE} = 1.8 V VOS[1:0] = 01	Range 2, V _{CORE} = 1.5 V VOS[1:0] = 10	Range 3, V _{CORE} = 1.2 V VOS[1:0] = 11	Low-power sleep and run	
APB2	SYSCFG & RI	3.5	2.9	2.4	2.9	μA/MHz (f _{HCLK})
	TIM9	9.0	7.4	5.8	7.4	
	TIM10	7.1	5.8	4.6	5.8	
	TIM11	6.5	5.3	4.3	5.3	
	ADC ⁽²⁾	11.0	9.1	7.2	9.1	
	SPI1	5.1	4.2	3.3	4.2	
	USART1	9.4	7.8	6.1	7.8	
AHB	GPIOA	7.3	6.1	4.8	6.1	
	GPIOB	7.5	6.1	4.8	6.1	
	GPIOC	8.2	6.8	5.3	6.8	
	GPIOD	8.7	7.1	5.7	7.1	
	GPIOE	7.6	6.2	4.9	6.2	
	GPIOF	7.7	6.3	5.0	6.3	
	GPIOG	8.4	7.0	5.4	7.0	
	GPIOH	1.8	1.3	1.1	1.3	
	CRC	0.8	0.6	0.4	0.6	
	AES	5	4	3	4	
	FLASH	26.3	19.3	18.3	_(3)	
	DMA1	19.0	16.0	12.8	16.0	
	DMA2	17.0	14.5	11.5	14.5	
All enabled		266	210	187	190.7	
I _{DD} (RTC)		0.4				μA
I _{DD} (LCD)		3.1				
I _{DD} (ADC) ⁽⁴⁾		1450				
I _{DD} (DAC) ⁽⁵⁾		340				
I _{DD} (COMP1)		0.16				
I _{DD} (COMP2)	Slow mode	2				
	Fast mode	5				
I _{DD} (PVD / BOR) ⁽⁶⁾		2.6				
I _{DD} (IWDG)		0.25				

Multi-speed internal (MSI) RC oscillator

Table 32. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at $V_{\text{DD}} = 3.3 \text{ V}$ and $T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$	MSI range 0	65.5	-	kHz
		MSI range 1	131	-	
		MSI range 2	262	-	
		MSI range 3	524	-	
		MSI range 4	1.05	-	MHz
		MSI range 5	2.1	-	
		MSI range 6	4.2	-	
ACC_{MSI}	Frequency error after factory calibration	-	± 0.5	-	%
$D_{\text{TEMP}(\text{MSI})}^{(1)}$	MSI oscillator frequency drift $0 \text{ }^{\circ}\text{C} \leq T_{\text{A}} \leq 105 \text{ }^{\circ}\text{C}$	-	± 3	-	%
$D_{\text{VOLT}(\text{MSI})}^{(1)}$	MSI oscillator frequency drift $1.65 \text{ V} \leq V_{\text{DD}} \leq 3.6 \text{ V}$, $T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$	-	-	2.5	%/V
$I_{\text{DD}(\text{MSI})}^{(2)}$	MSI oscillator power consumption	MSI range 0	0.75	-	μA
		MSI range 1	1	-	
		MSI range 2	1.5	-	
		MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
$t_{\text{SU}(\text{MSI})}$	MSI oscillator startup time	MSI range 0	30	-	μs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	

Figure 19. I²C bus AC waveforms and measurement circuit

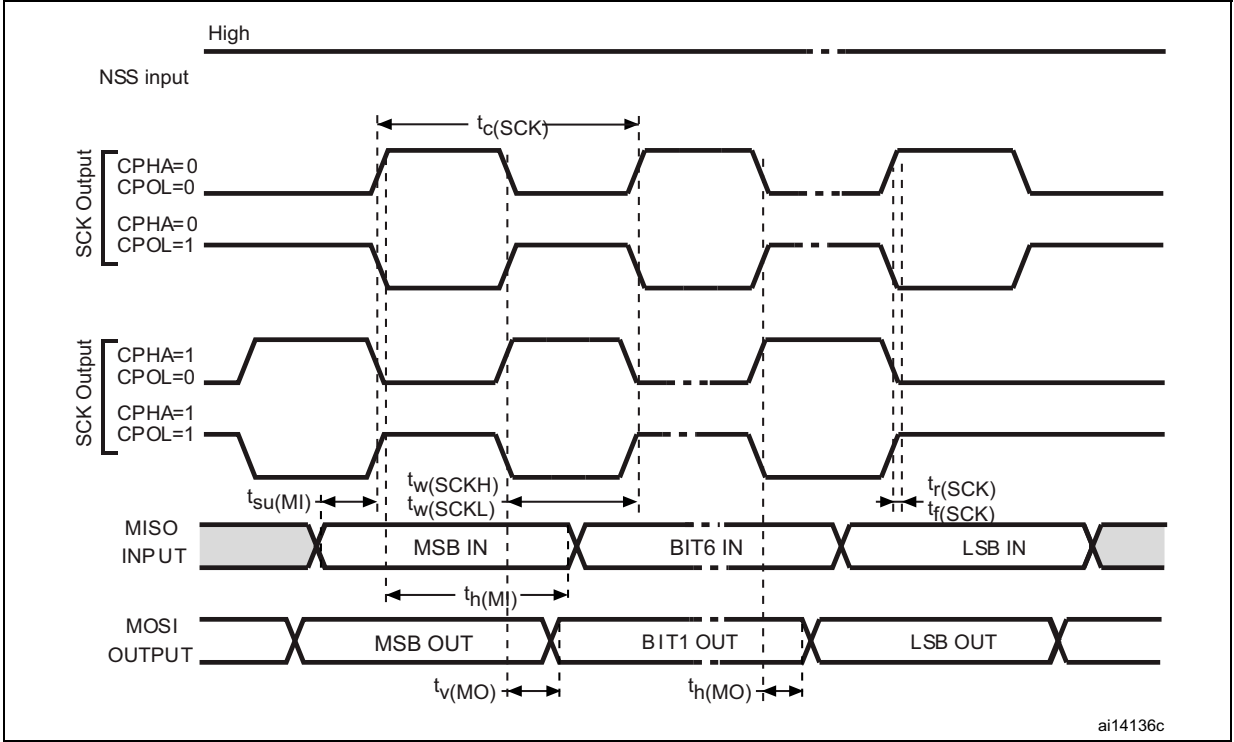
1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I2C bus power supply.
4. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 48. SCL frequency ($f_{PCLK1} = 32 \text{ MHz}$, $V_{DD} = V_{DD_I2C} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

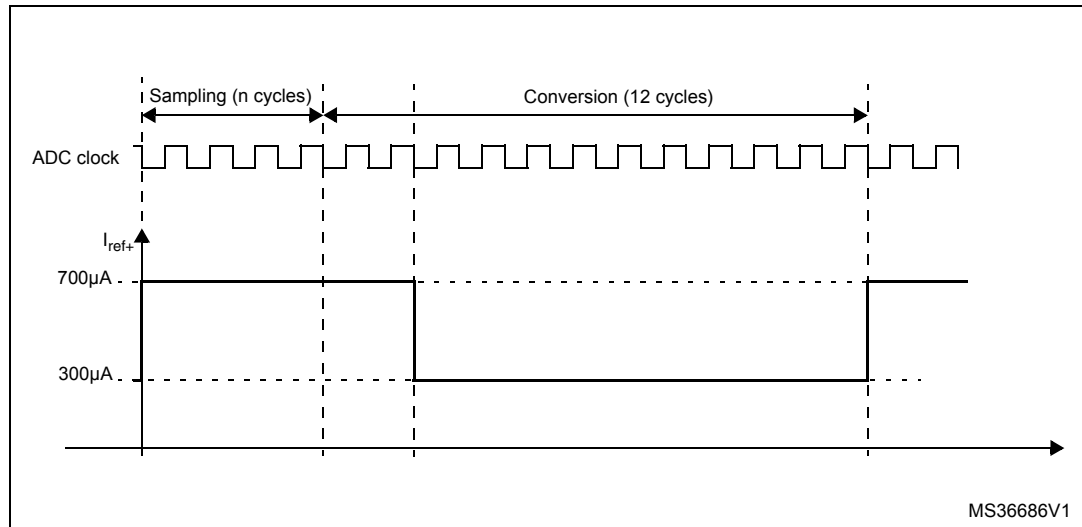
f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7 \text{ k}\Omega$
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

1. R_P = External pull-up resistance, f_{SCL} = I²C speed.
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed is $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

Figure 22. SPI timing diagram - master mode⁽¹⁾



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 28. Maximum dynamic current consumption on V_{REF+} supply pin during ADC conversion**Table 57. Maximum source impedance $R_{AIN\ max}^{(1)}$**

Ts (μs)	RAIN max (kΩ)				Ts (cycles) fADC=16 MHz ⁽²⁾
	Multiplexed channels		Direct channels		
	2.4 V < VDDA < 3.6 V	1.8 V < VDDA < 2.4 V	2.4 V < VDDA < 3.6 V	1.8 V < VDDA < 2.4 V	
0.25	Not allowed	Not allowed	0.7	Not allowed	4
0.5625	0.8	Not allowed	2.0	1.0	9
1	2.0	0.8	4.0	3.0	16
1.5	3.0	1.8	6.0	4.5	24
3	6.8	4.0	15.0	10.0	48
6	15.0	10.0	30.0	20.0	96
12	32.0	25.0	50.0	40.0	192
24	50.0	50.0	50.0	50.0	384

1. Guaranteed by design.

2. Number of samples calculated for $f_{ADC} = 16\ MHz$. For $f_{ADC} = 8$ and $4\ MHz$ the number of sampling cycles can be reduced with respect to the minimum sampling time T_s (μs),

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 10](#). The applicable procedure depends on whether V_{REF+} is connected to V_{DDA} or not. The $100\ nF$ capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

6.3.20 Temperature sensor characteristics

Table 60. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ± 5 °C $V_{DDA} = 3 \text{ V} \pm 10 \text{ mV}$	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ± 5 °C $V_{DDA} = 3 \text{ V} \pm 10 \text{ mV}$	0x1FF8 00FE - 0x1FF8 00FF

Table 61. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope ⁽¹⁾	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ± 5 °C ⁽²⁾	612	626.8	641.5	mV
$I_{DDA(TEMP)}^{(3)}$	Current consumption	-	3.4	6	μA
$t_{START}^{(3)}$	Startup time	-	-	10	μs
$T_{S_temp}^{(3)}$	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.

2. Measured at $V_{DD} = 3 \text{ V} \pm 10 \text{ mV}$. V_{110} ADC conversion result is stored in the TS_CAL2 byte.

3. Guaranteed by design.

6.3.21 Comparator

Table 62. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	μs
t_d	Propagation delay ⁽²⁾	-	-	3	10	
V_{offset}	Comparator offset	-	-	± 3	± 10	mV
$d_{V_{offset}}/dt$	Comparator offset variation in worst voltage stress conditions	$V_{DDA} = 3.6 \text{ V}$ $V_{IN+} = 0 \text{ V}$ $V_{IN-} = V_{REFINT}$ $T_A = 25 \text{ °C}$	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

1. Guaranteed by characterization results.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage not included.

Table 63. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.65	-	3.6	V
V_{IN}	Comparator 2 input voltage range	-	0	-	V_{DDA}	V
t_{START}	Comparator startup time	Fast mode	-	15	20	μs
		Slow mode	-	20	25	
$t_{d\ slow}$	Propagation delay ⁽²⁾ in slow mode	$1.65\ V \leq V_{DDA} \leq 2.7\ V$	-	1.8	3.5	
		$2.7\ V \leq V_{DDA} \leq 3.6\ V$	-	2.5	6	
$t_{d\ fast}$	Propagation delay ⁽²⁾ in fast mode	$1.65\ V \leq V_{DDA} \leq 2.7\ V$	-	0.8	2	
		$2.7\ V \leq V_{DDA} \leq 3.6\ V$	-	1.2	4	
V_{offset}	Comparator offset error		-	± 4	± 20	mV
$dThreshold/dt$	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$ $T_A = 0\ to\ 50\ ^\circ C$ $V_- = V_{REFINT},$ $3/4\ V_{REFINT},$ $1/2\ V_{REFINT},$ $1/4\ V_{REFINT}.$	-	15	100	ppm/ $^\circ C$
I_{COMP2}	Current consumption ⁽³⁾	Fast mode	-	3.5	5	μA
		Slow mode	-	0.5	2	

1. Guaranteed by characterization results.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

Table 65. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.4 UFBGA132, 7 x 7 mm, 132-ball ultra thin, fine-pitch ball grid array package information

Figure 39. UFBGA132, 7 x 7 mm, 132-ball ultra thin, fine-pitch ball grid array package outline

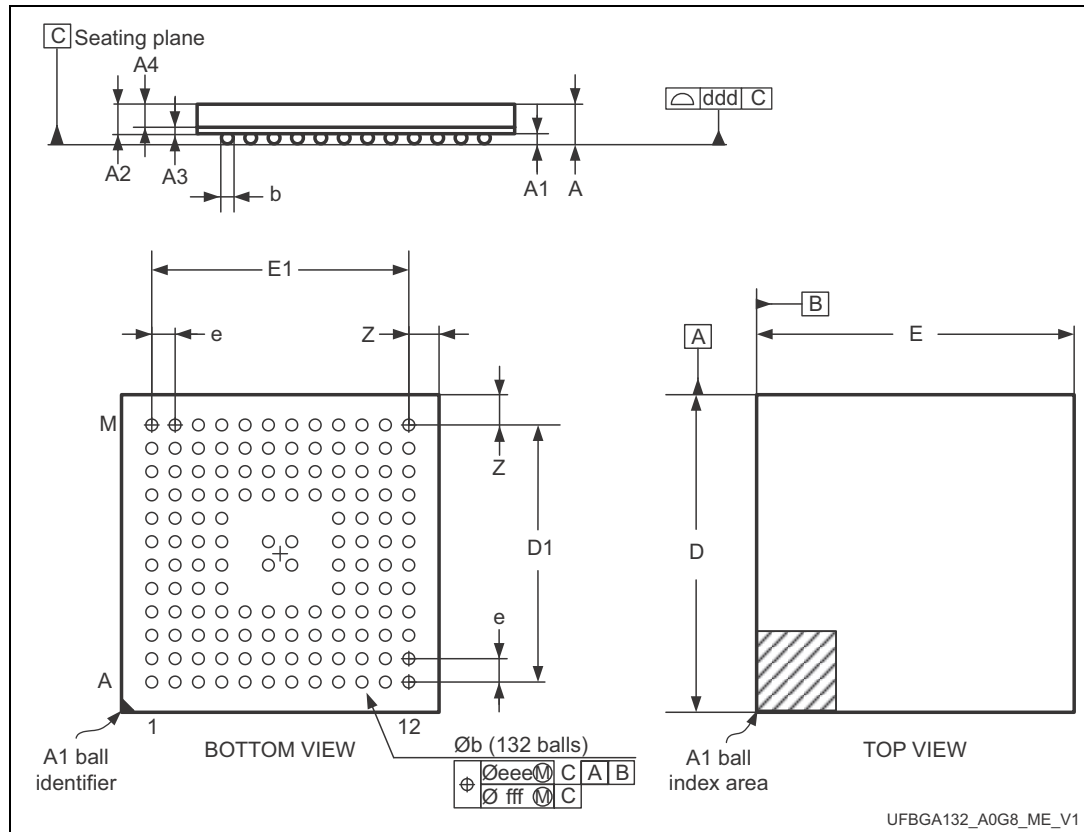
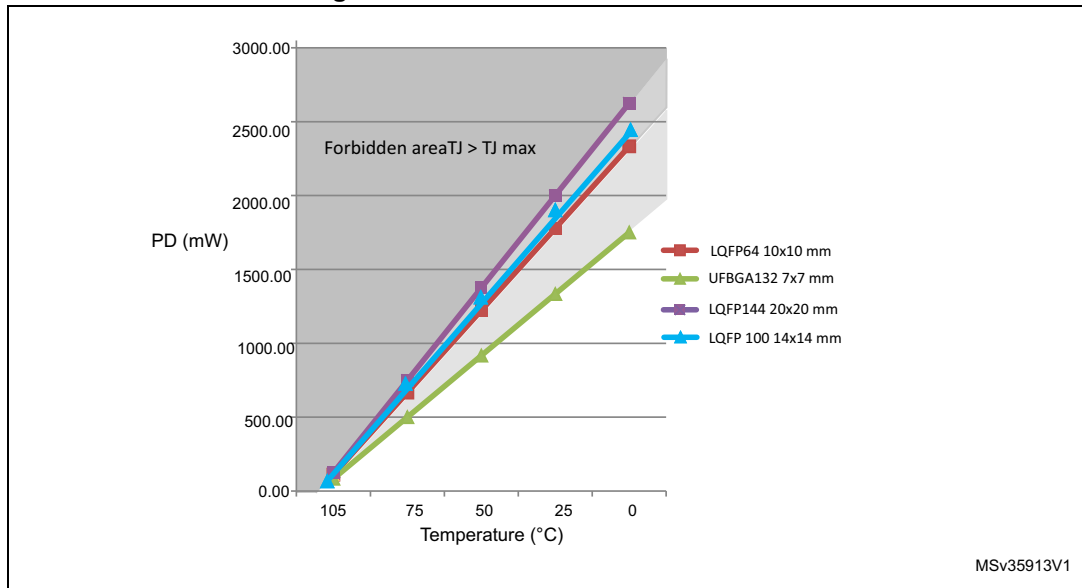


Table 68. UFBGA132, 7 x 7 mm, 132-ball ultra thin, fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.170	0.280	0.330	0.0067	0.0110	0.0130
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
e	-	0.500	-	-	0.0197	-
F	0.700	0.750	0.800	0.0276	0.0295	0.0315

Figure 43. Thermal resistance suffix 7



7.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

9 Revision History

Table 71. Document revision history

Date	Revision	Changes
21-May-2014	1	Initial release
12-Sept-2014	2	Updated communication interfaces section including I2S characteristics. Updated DMIPS features in cover page and description section. Updated -40°C to 105°C temperature range. Updated Flash switched ON & OFF modes Updated peripheral consumption table. Updated maximum source impedance RAIN max.
02-Mar-2015	3	Updated Section 7: Package information with new package device marking. Updated Figure 7: Memory map .
18-Mar-2016	4	Updated Table 16: Embedded internal reference voltage temperature coefficient at 100ppm/°C. and table note 3: “guaranteed by design” changed by “guaranteed by characterization results”. Updated Table 63: Comparator 2 characteristics new maximum threshold voltage temperature coefficient at 100ppm/°C. Updated Table 8: STM32L162xC/C-A pin definitions ADC inputs. Updated cover page putting eight SPIs in the peripheral communication interface list. Updated Table 2: Ultra-low-power STM32L162xC/C-A device features and peripheral counts SPI and I2S lines. Updated Table 39: ESD absolute maximum ratings CDM class. Updated all the notes, removing ‘not tested in production’. Updated Table 10: Voltage characteristics adding note about V _{REF} -pin. Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby) LSI and LSE functionalities putting “Y” in Standby mode. Removed note 1 below Figure 2: Clock tree .

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